FAIRCHILD SEMICONDUCTOR®

April 2013

FQD1N80 / FQU1N80

N-Channel QFET® MOSFET

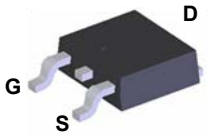
800 V, 1.0 A, 20 Ω

Description

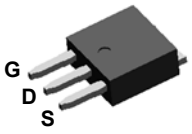
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

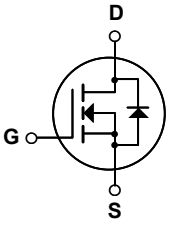
- 1.0 A, 800 V, $R_{DS(on)}$ = 20 Ω (Max.) @ V_{GS} = 10 V, I_D = 0.5 A
- Low Gate Charge (Typ. 5.5 nC)
- Low Crss (Typ. 2.7 pF)
- 100% Avalanche Tested



D-PAK



I-PAK



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQD1N80 / FQU1N80	Unit
V_{DSS}	Drain-Source Voltage		800	V
I_D	Drain Current - Continuous (T_C = 25°C)		1.0	A
	- Continuous (T_C = 100°C)		0.63	A
I_{DM}	Drain Current - Pulsed	(Note 1)	4.0	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	90	mJ
I_{AR}	Avalanche Current	(Note 1)	1.0	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns
P_D	Power Dissipation (T_A = 25°C) *		2.5	W
	Power Dissipation (T_C = 25°C)		45	W
	- Derate above 25°C		0.36	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQD1N80 / FQU1N80	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	800	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	1.0	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 640 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 0.5 A	--	15.5	20	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 0.5 A	--	0.75	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	150	195	pF
C_{oss}	Output Capacitance		--	20	26	pF
C_{rss}	Reverse Transfer Capacitance		--	2.7	3.5	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 1.0 A, R_G = 25 Ω	--	10	30	ns
t_r	Turn-On Rise Time		--	25	60	ns
$t_{d(off)}$	Turn-Off Delay Time		--	15	40	ns
t_f	Turn-Off Fall Time		--	25	60	ns
Q_g	Total Gate Charge	V_{DS} = 640 V, I_D = 1.0 A, V_{GS} = 10 V	--	5.5	7.2	nC
Q_{gs}	Gate-Source Charge		--	1.1	--	nC
Q_{gd}	Gate-Drain Charge		--	3.3	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	1.0	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	4.0	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.0 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 1.0 A, dI_F / dt = 100 A/μs	--	300	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.6	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 170mH, I_{AS} = 1.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. $I_{SD} \leq$ 1.0A, di/dt $\leq$ 200A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J = 25°C
4. Pulse Test : Pulse width $\leq$ 300μs, Duty cycle $\leq$ 2%
5. Essentially independent of operating temperature

Typical Characteristics

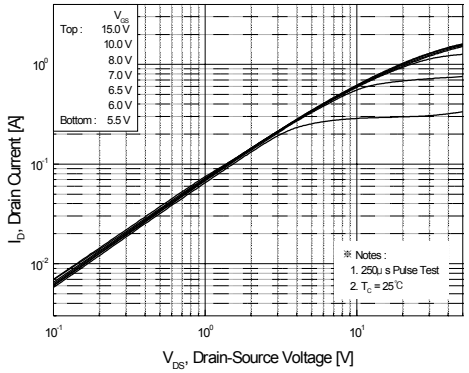


Figure 1. On-Region Characteristics

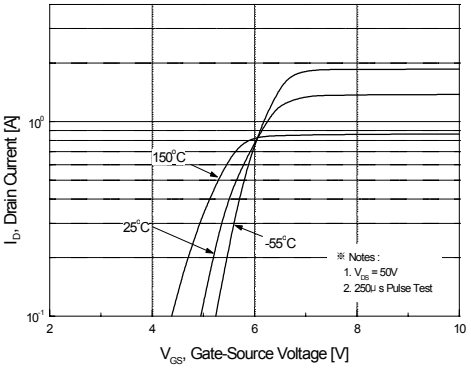


Figure 2. Transfer Characteristics

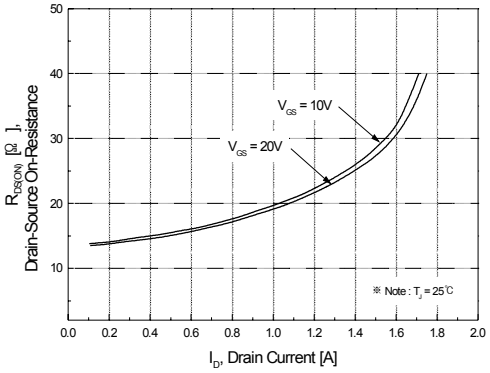


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

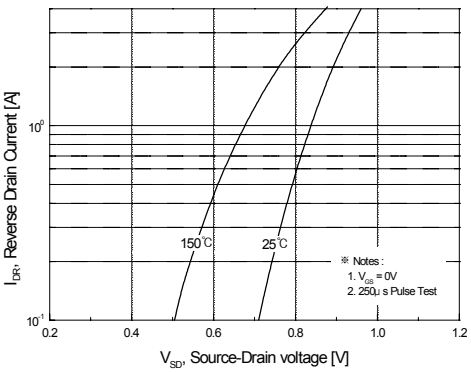


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

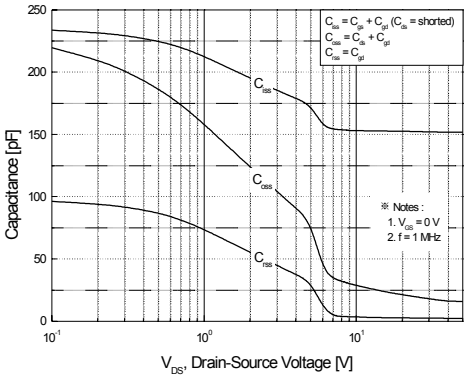


Figure 5. Capacitance Characteristics

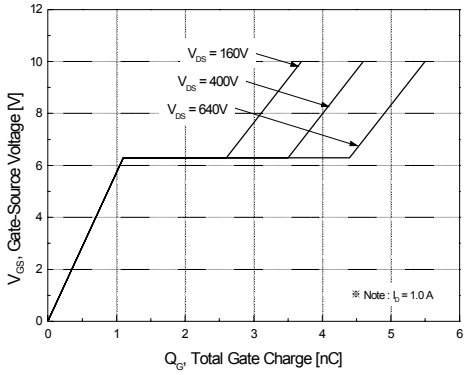


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

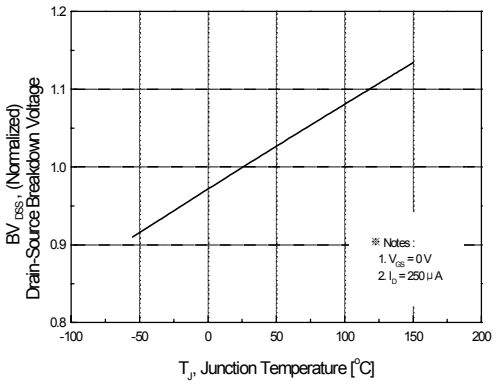


Figure 7. Breakdown Voltage Variation vs. Temperature

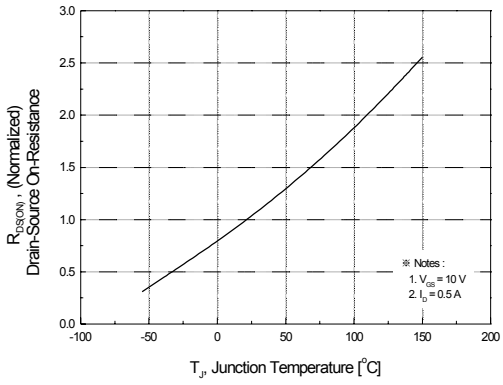


Figure 8. On-Resistance Variation vs. Temperature

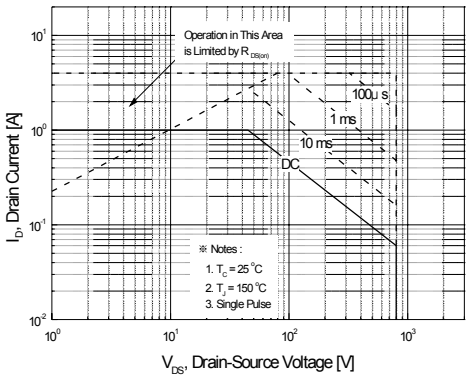


Figure 9. Maximum Safe Operating Area

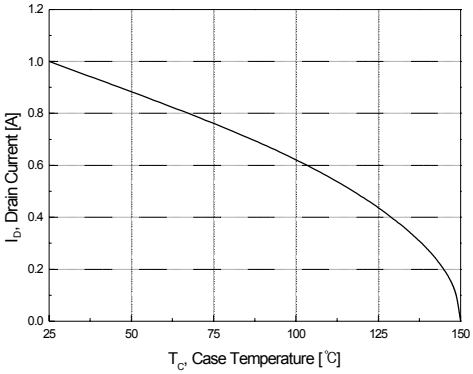


Figure 10. Maximum Drain Current vs. Case Temperature

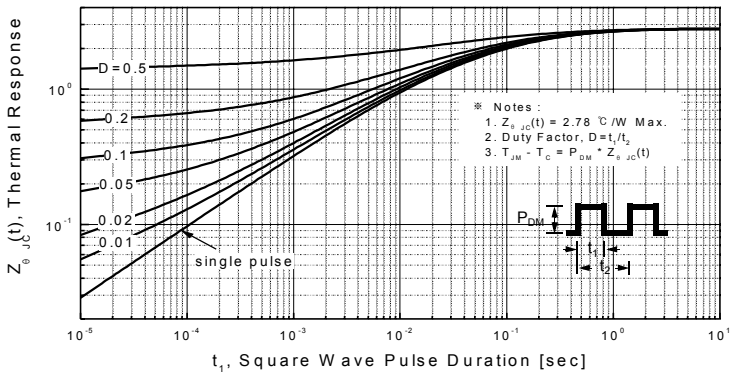
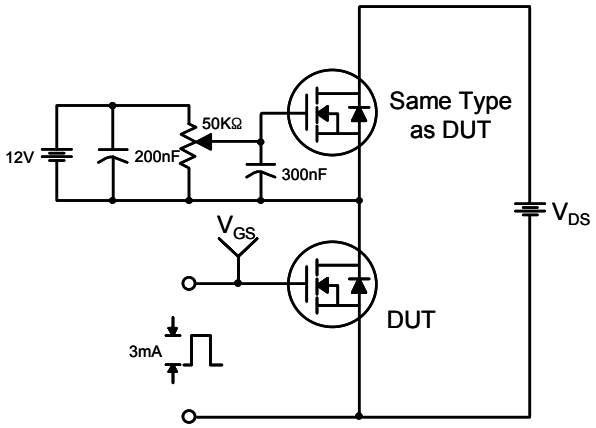
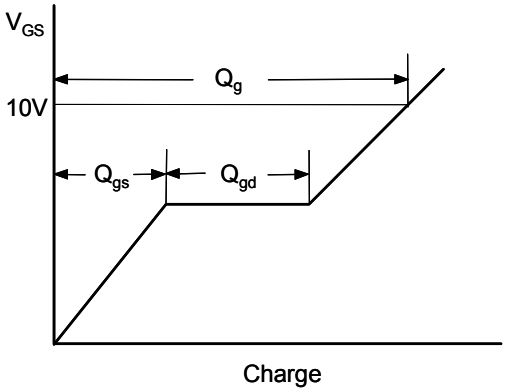


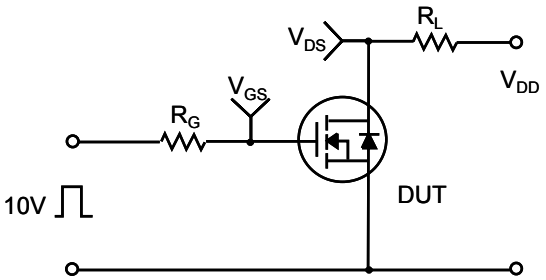
Figure 11. Transient Thermal Response Curve

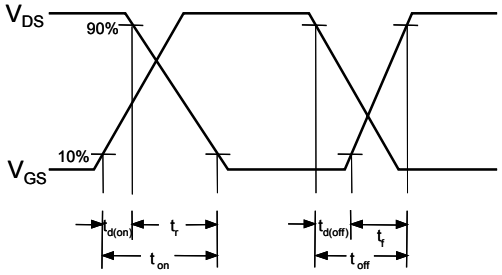
Gate Charge Test Circuit & Waveform



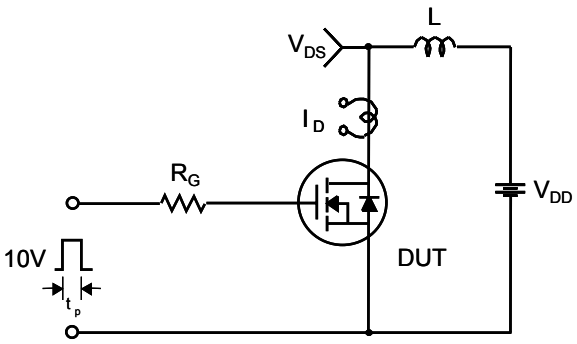


Resistive Switching Test Circuit & Waveforms

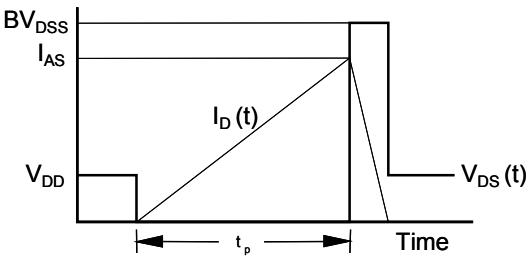




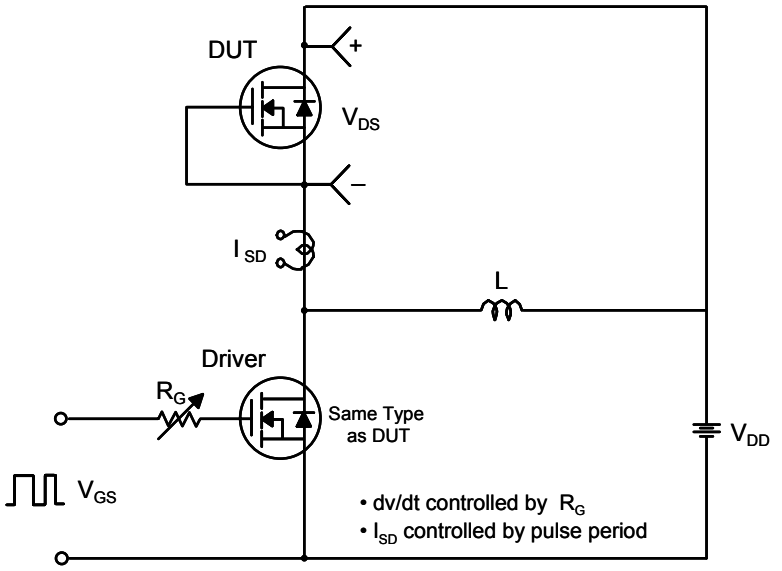
Unclamped Inductive Switching Test Circuit & Waveforms

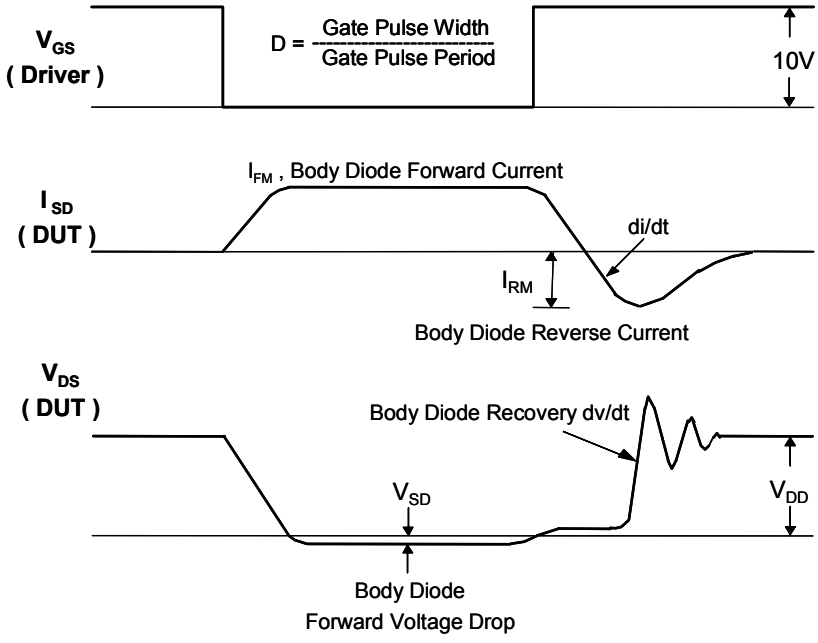


$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



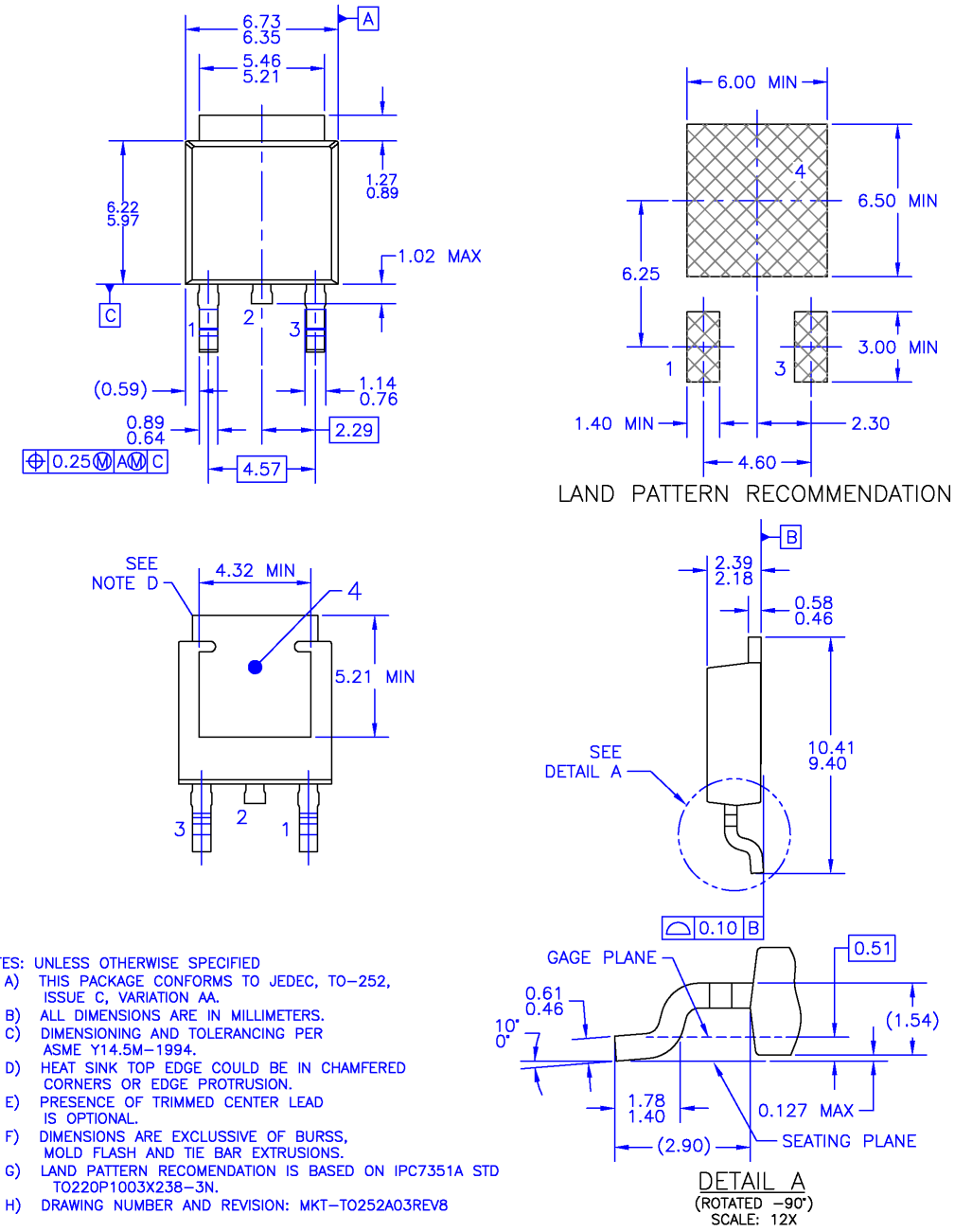
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

D-PAK



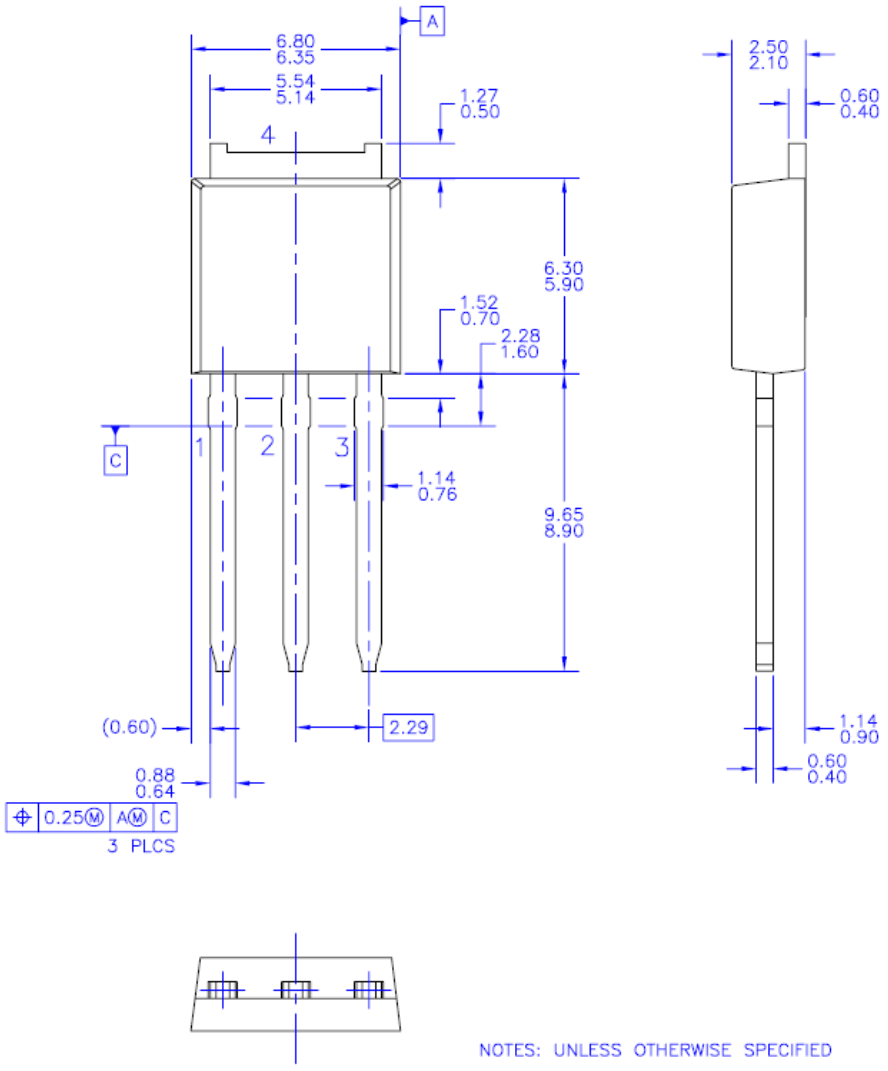
NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO JEDEC, TO−252, ISSUE C, VARIATION AA.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M−1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.
F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO220P1003X238−3N.
H) DRAWING NUMBER AND REVISION: MKT−TO252A03REV8

Dimensions in Millimeters

Mechanical Dimensions

I-PAK



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) THIS PACKAGE CONFORMS TO JEDEC, TO-251, ISSUE C, VARIATION AA, DATED SEP 1988.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

Dimensions in Millimeters

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™
AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource^{SM}
Green Bridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver™
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL ®*
TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC®
TriFault Detect™
TRUECURRENT®*
µSerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64